

54F/74F821 10-Bit D-Type Flip-Flop

General Description

The 'F821 is a 10-bit D-type flip-flop with TRI-STATE® true outputs arranged in a broadside pinout. The 'F821 is functionally and pin compatible with the AMD's Am29821.

Features

- TRI-STATE Outputs
- Direct replacement for AMD's Am29821

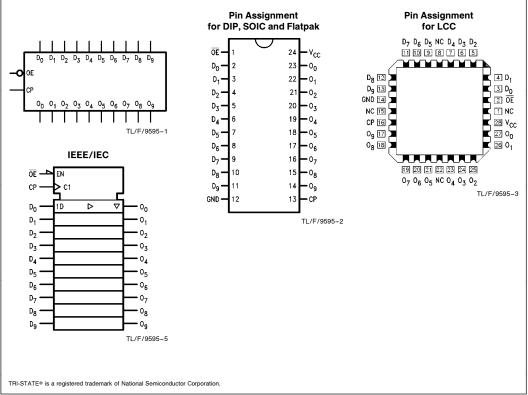
Commercial	Military	Package Number	Package Description		
74F821SPC		N24C	24-Lead (0.300" Wide) Molded Dual-In-Line		
	54F821SDM (Note 2)	J24F	24-Lead (0.300" Wide) Ceramic Dual-In-Line		
74F821SC (Note 1)		M24B	24-Lead (0.300" Wide) Molded Small Outline, JEDEC		
	54F821FM (Note 2)	W24C	24-Lead Cerpack		
	54F821LM (Note 2)	E28A	24-Lead Ceramic Leadless Chip Carrier, Type C		

Note 1: Devices also available in 13" reel. Use suffix = SCX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = SDMQB, FMQB and LMQB.

Logic Symbols

Connection Diagrams



Unit Loading/Fan Out

		54F/74F					
Pin Names Description		U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}				
D ₀ -D ₉	Data Inputs	1.0/1.0	20 μA/-0.6 mA				
ŌĒ	Output Enable TRI-STATE Input	1.0/1.0	20 μA/ - 0.6 mA				
CP	Clock Input	1.0/1.0	20 μA/ – 0.6 mA				
O ₀ -O ₉	TRI-STATE Outputs	150/40 (33.3)	-3.0 mA/24 mA (20 mA)				

Functional Description

The 'F821 consists of ten D-type edge-triggered flip-flops. This device has TRI-STATE true outputs for bus systems organized in a broadside pinning. The buffered Clock (CP) and buffered Output Enable (\overline{OE}) are common to all flipflops. The flip-flops will store the state of their individual D inputs that meet the setup and hold times requirements on the LOW-to-HIGH CP transition. With the $\overline{\text{OE}}$ LOW the content of the flip-flops are available at the outputs. When the $\overline{\text{OE}}$ is HIGH, the outputs go to the high impedance state. Operation of the $\overline{\text{OE}}$ input does not affect the state of the flip-flops.

Function Table

I	Inputs		Internal	Output	Function			
ŌĒ	СР	D	Q	0	T dilotion			
H H	H L	X X	NC NC	Z Z	Hold Hold			
Н	\mathcal{L}	L	Н	Z	Load			
Н	\mathcal{L}	Н	L	Z	Load			
L		L	Н	L	Data Available			
L	\mathcal{L}	Н	L	Н	Data Available			
L	Н	Х	NC	NC	No Change in Data			
L	L	Х	NC	NC	No Change in Data			

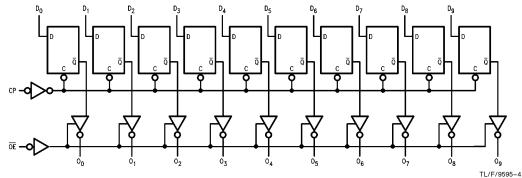
L = LOW Voltage Level

H = HIGH Voltage Level X = Immaterial

Z = High Impedance

✓ = LOW-to-HIGH Transition NC = No Change

Logic Diagram



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Storage Temperature} & -65^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \mbox{Ambient Temperature under Bias} & -55^{\circ}\mbox{C to} + 125^{\circ}\mbox{C} \\ \mbox{Junction Temperature under Bias} & -55^{\circ}\mbox{C to} + 175^{\circ}\mbox{C} \\ \mbox{Plastic} & -55^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \end{array}$

V_{CC} Pin Potential to

Ground Pin -0.5V to +7.0V Input Voltage (Note 2) -0.5V to +7.0V Input Current (Note 2) -30 mA to +5.0 mA

Voltage Applied to Output in HIGH State (with $V_{CC} = 0V$)

 $\begin{array}{ll} \text{Standard Output} & -0.5 \text{V to V}_{\text{CC}} \\ \text{TRI-STATE Output} & -0.5 \text{V to } +5.5 \text{V} \end{array}$

Current Applied to Output

in LOW State (Max) twice the rated I_{OL} (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature

Military $-55^{\circ}\text{C to} + 125^{\circ}\text{C}$ Commercial $0^{\circ}\text{C to} + 70^{\circ}\text{C}$

Supply Voltage

Military + 4.5V to + 5.5V Commercial + 4.5V to + 5.5V

DC Electrical Characteristics

Symbol	Parameter .		54F/74F			Units	Vcc	Conditions	
Syllibol			Min	Тур	Max	Units	VCC	Conditions	
V _{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signa	
V_{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signa	
V _{CD}	Input Clamp Diode Voltage				-1.2	V	Min	$I_{\text{IN}} = -18 \text{mA}$	
V _{OH}	Output HIGH Voltage	54F 10% V _{CC} 54F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC} 74F 5% V _{CC}	2.5 2.4 2.5 2.4 2.7 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -3 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -3 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -3 \text{ mA}$	
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}			0.5 0.5	٧	Min	I _{OL} = 20 mA I _{OL} = 24 mA	
I _{IH}	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	$V_{IN} = 2.7V$	
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	$V_{IN} = 7.0V$	
I _{CEX}	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
V_{ID}	Input Leakage Test	74F	4.75			٧	0.0	$I_{\text{ID}} = 1.9 \mu\text{A},$ All Other Pins Grounded	
l _{OD}	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V _{IOD} = 150 mV All Other Pins Grounded	
I _{IL}	Input LOW Current				-0.6	mA	Max	V _{IN} = 0.5V	
l _{OZH}	Output Leakage Current				50	μΑ	Max	V _{OUT} = 2.7V	
lozL	Output Leakage Current				-50	μΑ	Max	$V_{OUT} = 0.5V$	
los	Output Short-Circuit Current		-60		-150	mA	Max	$V_{OUT} = 0V$	
Iccz	Power Supply Curren	t		78	100	mA	Max	V _O = HIGH Z	

AC Electrical Characteristics

Symbol	Parameter	$74F$ $T_{A} = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 \text{ pF}$			54F T _A , V _{CC} = Mil C _L = 50 pF		74F T _A , V _{CC} = Com C _L = 50 pF		Units
		Min	Тур	Max	Min	Max	Min	Max	
f _{max}	Maximum Clock Frequency	100	150		60		70		MHz
t _{PLH} t _{PHL}	Propagation Delay CP to O _n	2.0 2.0	6.4 6.2	9.5 9.5	2.0 2.0	10.5 10.5	2.0 2.0	10.5 10.5	ns
t _{PZH}	Output Enable Time OE to On	2.0 2.0	5.8 6.3	10.5 10.5	2.0 2.0	13.0 13.0	2.0 2.0	11.5 11.5	ns
t _{PHZ}	Output Disable Time OE to On	1.5 1.5	3.4 3.5	7.0 7.0	1.0 1.0	7.5 7.5	1.5 1.5	7.5 7.5	115

AC Operating Requirements

		$74F$ $T_A = +25^{\circ}C$ $V_{CC} = +5.0V$		54	F	74F		
Symbol	Parameter			${\sf T_A,V_{CC}}={\sf Mil}$		T _A , V _{CC} = Com		Units
		Min	Max	Min	Max	Min	Max	
t _s (H) t _s (L)	Setup Time, HIGH or LOW D _n to CP	2.5 2.5		4.0 4.0		3.0 3.0		- ns
t _h (H) t _h (L)	Hold Time, HIGH or LOW D _n to CP	2.5 2.5		2.5 2.5		2.5 2.5		
t _w (H)	CP Pulse Width HIGH or LOW	5.0 5.0		6.0 6.0		6.0 6.0		ns

Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

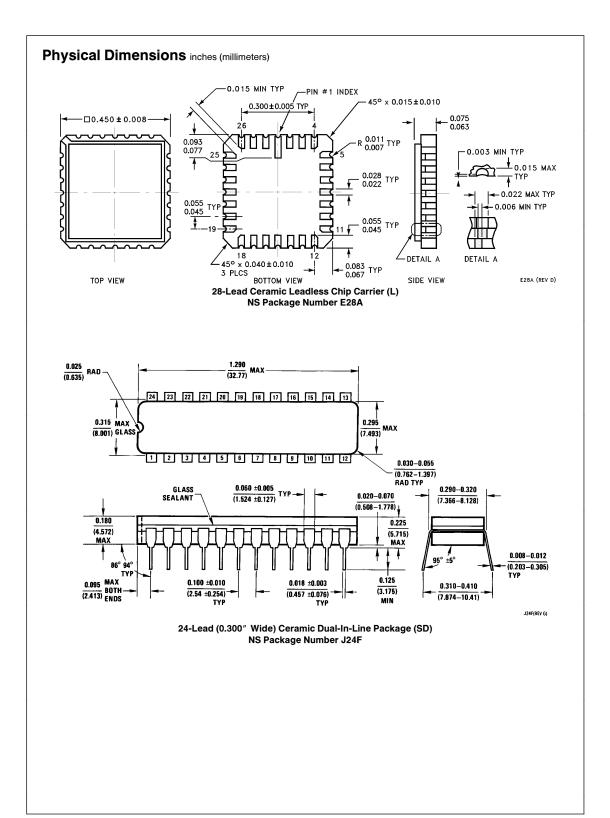
Temperature Range Family
74F = Commercial FAST
54F = Military FAST

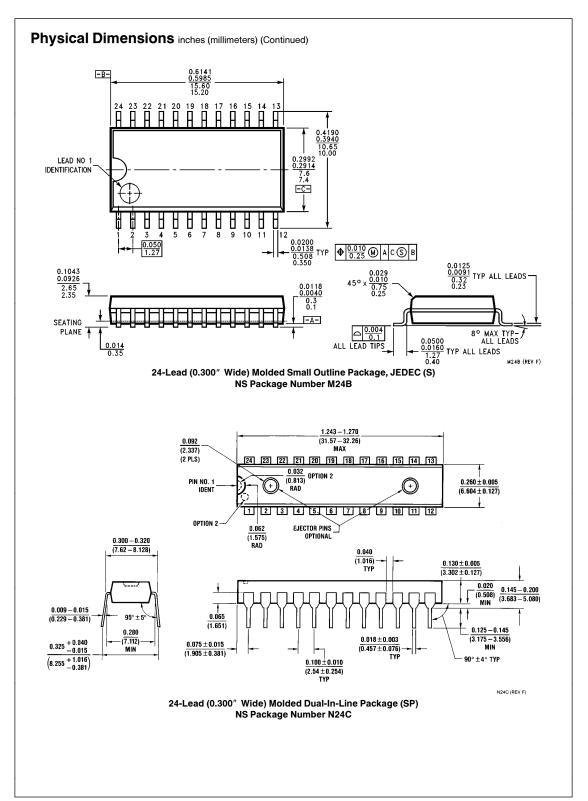
Device Type
Package Code
SP = Slim Plastic DIP
SD = Slim Ceramic DIP

Temperature Range
C = Commercial (0°C to +70°C)
M = Military grade device with environmental and burn-in processing
X = Devices ship in 13" reel

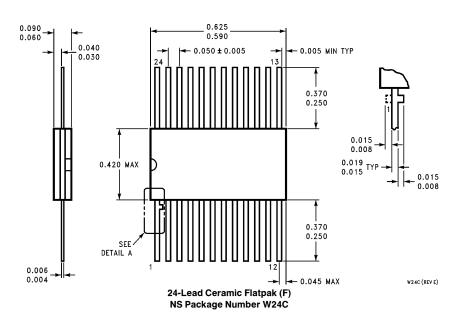
Temperature Range
C = Commercial (0°C to +70°C)
M = Military (-55°C to +125°C)

F = Flatpak
L = Leadless Chip Carrier (LCC)
S = Small Outline (SOIC)





Physical Dimensions inches (millimeters) (Continued)



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